

FEATURES

for general purpose, high volt

As complementary types the PNP transistors 2N5401 are recommended.

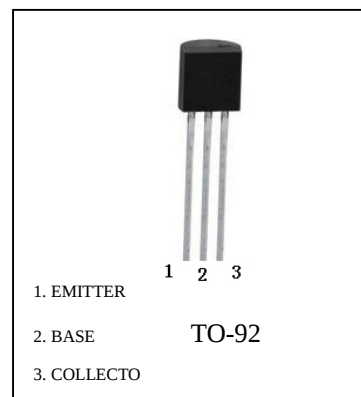
Low current(max. 600mA),High voltage(max.180V)

MARKING:2N5551

MAXIMUM RATINGS (TA=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_C	600	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C

2N5551 (NPN)



ELECTRICAL CHARACTERISTICS (Tamb=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	180			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=1mA, I_B=0$	160			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=10\mu A, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=120V, I_E=0$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			50	nA
DC current gain	h_{FE1}	$V_{CE}=5V, I_C=1mA$	80			
	h_{FE2}	$V_{CE}=5V, I_C=10mA$	100		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.15	V
		$I_C=50mA, I_B=5mA$			0.2	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1	V
		$I_C=50mA, I_B=5mA$			1	
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA, f=100MHz$	100		300	MHz
Collector output capacitance	C_{obo}	$V_{CB}=10V, I_E=0, f=1MHz$			6	pF
Input capacitance	C_{ib}	$V_{BE}=0.5V, I_C=0, f=1MHz$			20	pF
Noise figure	N_F	$V_{CE}=5V, I_C=0.25mA, f=10Hz \text{ to } 15.7KHz, R_s=1k\Omega$			8	dB

CLASSIFICATION OF HFE

Rank	A	B	C
Range	100-150	150-200	200-300

2N5551 Typical Characteristics

Fig. 1 $P_C - T_a$

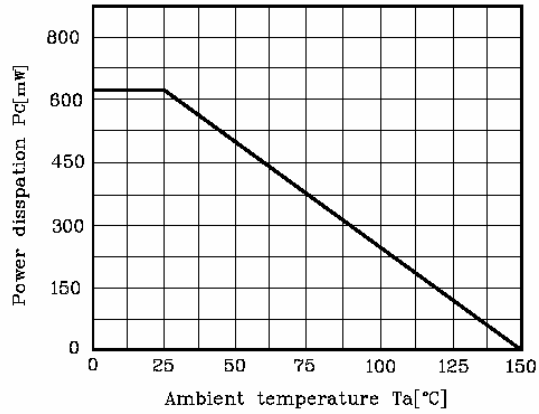


Fig. 2 $I_C - V_{BE}$

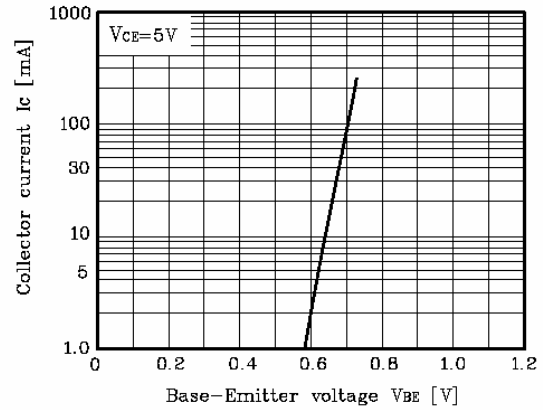


Fig. 3 $f_T - I_C$

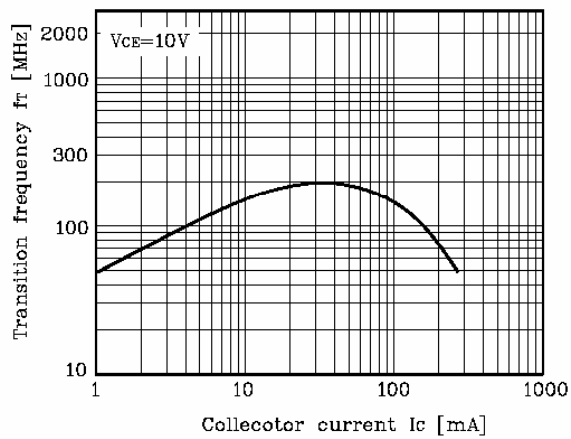


Fig. 4 $V_{CE(sat)}, V_{BE(sat)} - I_C$

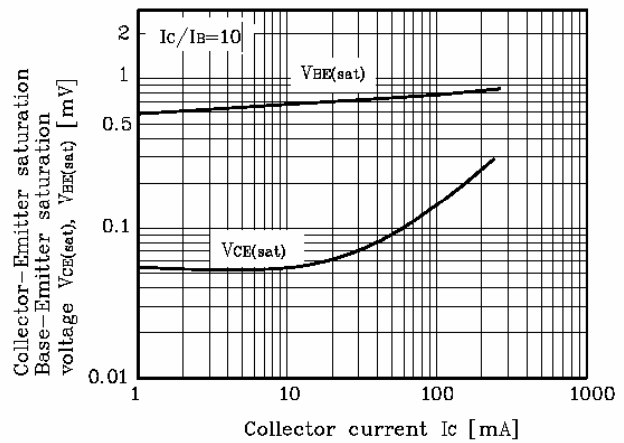


Fig. 5 $C_{ob} - V_{CB}$

